

[MoA2] Advanced Growth Techniques - I

Session Date	July 13 (Mon.), 2026
Session Time	14:00–15:45
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Prof. Zhe Zhuang (Nanjing University, China), Prof. Michael Heuken (AIXTRON, RWTH Aachen University, Germany)

[MoA2–1] [Invited]

14:00–14:30

Remote Epitaxy of Deformable and Stacktronic Devices

Young Joon Hong, Sungkyunkwan University, Korea

[MoA2–2]

14:30–14:45

Fabrication of Wafer-Scale Freestanding GaN Membrane Utilizing Transfer-Free Thin Amorphous Carbon Layer via MOCVD-Based Remote Epitaxy

Joonghoon Choi, Wonkwang Yang, Chang Soo Kim, Junhyun Bae, and Young Joon Hong, Sungkyunkwan University, Korea

[MoA2–3]

14:45–15:00

Remote Epitaxy of α -Ga₂O₃ via Polycrystalline MoS₂

Gyeong Ryul Lee and Roy. B. Chung, Kyungpook National University, Korea

[MoA2–4]

15:00–15:15

MOCVD of GaN and AlGaIn/GaN Heterostructures on Si(001) by Wafer-Scale MoS₂ Templates

Seung Hoon Lee¹, Chen Chen¹, Brian M. Bersch², and Joan M. Redwing¹, ¹Pennsylvania State University, USA, ²Northrop Grumman Mission Systems, USA

[MoA2–5]

15:15–15:30

InGaIn Quantum Wells Grown on Spatially Patterned Substrates – Towards the 3D Laser Emitters

Grzanka Ewa, Grzanka Szymon, Robert Czernecki, Mikołaj Grabowski, Roman Hrytsak, Artur Lachowski, Julita Smalc-Koziorowska, and Michał Leszczynski, Institute of High Pressure Physics, Poland

Room-Temperature Continuous-Wave III-V/Si PhC Lasers on SOI Using Selective Lateral Heteroepitaxy

Xingyu Yang, Yao Chen, Jinglong Chen, Siyuan Yu, and Yu Han, Sun Yat-sen University, China